

III B. Tech II Semester Regular Examinations, April/May - 2019

VLSI DESIGN

(Common to Electronics and Communication Engineering, Electronics and Instrumentation Engineering, Electronics and Computer Engineering)

Time: 3 hours

Max. Marks: 70

- Note: 1. Question Paper consists of two parts (**Part-A** and **Part-B**)
 2. Answer **ALL** the question in **Part-A**
 3. Answer any **FOUR** Questions from **Part-B**

PART -A

1. a) Write down the equations for I_{ds} of an n-channel enhancement MOSFET operating in Non-saturated region and saturated region. [2M]
- b) Define stick diagram and layout diagram. [2M]
- c) Explain about the constraints in choice of layers. [2M]
- d) Mention the common techniques involved in ad-hoc testing. [3M]
- e) What information from the targeted FPGA device is required in RTL synthesis? [3M]
- f) Explain about clock skew. [2M]

PART -B

2. a) Explain the nMOS enhancement mode fabrication process for different conditions of V_{ds} . [7M]
- b) Derive an expression for transconductance of an n-channel enhancement MOSFET operating in active region. [7M]
3. a) Draw a stick diagram and layout for two input CMOS NAND gate indicating all the regions and layers. [7M]
- b) Explain 2 μ m Double Metal, Double Poly CMOS / BiCMOS Rules. [7M]
4. a) Explain the issues involved in driving large capacitor loads in VLSI circuit regions. [7M]
- b) Calculate the gate capacitance value of 5 mm technology minimum size transistor with gate to channel value is 4×10^{-4} pF/mm². [7M]
5. a) Explain about the following types of faults with suitable example: [7M]
 (i) stuck at faults (ii) Bridge faults (iii) temporary faults
- b) Explain the different categories of DFT techniques. [7M]
6. a) Write down the step by step approach for FPGA design process on XILINX environment? [7M]
- b) Draw and explain the basic architecture of FPGA. [7M]
7. a) Explain about deep submicron processes with suitable schematic diagrams. [7M]
- b) Explain about the scaling limitation for low voltage, low power design. Give the effect of scaling on various MOSFET parameters with necessary equations. [7M]



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PART -A

1. a) Explain the terms SSI, LSI, and VLSI with the number of transistors per chip and applications. [2M]
- b) Draw the stick diagram for CMOS Inverter. [2M]
- c) What is sheet resistance? Derive the Expression for R_s ? [2M]
- d) What are the approaches in design for testability? [3M]
- e) Explain synthesis process. [3M]
- f) What are the different types of power consumption? [2M]

PART -B

2. a) Explain in detail the p-well process for CMOS fabrication indicating the masks used. [7M]
- b) Compare the relative merits of three different forms of pull-up for an inverter circuit. What is the best choice for realization in nMOS and CMOS technology? [7M]
3. a) What are the λ -based design rules? Give them for each layer. [7M]
- b) Draw a stick diagram for CMOS logic $Y = (A+B+C)'$. [7M]
4. a) What is inverter delay? How delay is calculated for multiple stages? Explain. [7M]
- b) Two nMOS inverters are cascaded to drive a capacitive load $C_L = 16C_g$. Calculate pair delay V_{in} to V_{out} in terms of τ . [7M]
5. a) What are the different faults found in combinational circuits? How can they be categorized? [7M]
- b) Briefly discuss about Built-In-Self Test technique with a suitable diagram. [7M]
6. a) Give the steps in FPGA design flow with flow diagram and briefly discuss about each step. [7M]
- b) Explain about the principle and operation of FPGAs. What are its applications? [7M]
7. a) Discuss about the various problems associated with low voltage VLSI circuit design. [7M]
- b) Explain about estimation and optimization of switching activity. [7M]



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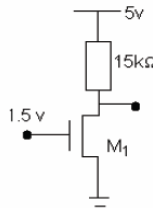
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PART -A

1. a) Define Moore's law. [2M]
- b) Draw a symbolic layout of a two-input NAND gate. [3M]
- c) Give the scaling factor for Maximum operating frequency (f_0) in terms of different scaling models. [2M]
- d) What is meant by observability? [3M]
- e) What are FPGAs? [2M]
- f) What is switching activity? [2M]

PART -B

2. a) Compare BiCMOS technology with other Technologies. [7M]
- b) Calculate I_D and V_{DS} if $k_n = 100 \mu A/V^2$, $V_{tn} = 0.6V$ and $W/L = 3$ for transistor M_1 , in the circuit shown below: [7M]



3. a) Explain with suitable examples how to design the layout of a Gate to maximize performance and minimize area. [7M]
- b) Design a stick diagram for nMOS logic $Y = (A+B+C)'$. [7M]
4. a) How does depletion regions around source and drain are affected due to scaling down of device dimensions? Explain. [7M]
- b) Derive the expression for propagation delay in the case of cascaded pass transistors. [7M]
5. a) Define the terms 'failure' and 'fault'. Discuss the different fault models. [7M]
- b) Briefly discuss about On-Chip clock generation and distribution. [7M]
6. a) Explain the following terms: [8M]
 (i) LUT (ii) CLB (iii) IOB (iv) Switch matrix
- b) List out the various FPGA families. Explain how they are different from each other? [6M]
7. a) Explain about the design limitations imposed on low power, low voltage circuits pertaining to the scaling and inter connect wires. [7M]
- b) Briefly discuss about the different techniques for reduction of switching capacitance. [7M]



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PART -A

- | | | | |
|----|----|---|------|
| 1. | a) | Discuss the microelectronics evolution. | [3M] |
| | b) | What is Vias? How to construct it in layout? | [2M] |
| | c) | What is the need of scaling in MOS circuits? | [2M] |
| | d) | Explain how function of system can be tested. | [2M] |
| | e) | List out the commercially available FPGAs. | [3M] |
| | f) | What is the need of interconnect? | [2M] |

PART -B

- | | | | |
|----|----|--|-------|
| 2. | a) | What are the additional two layers in BiCMOS technology compared to others? With neat sketches explain BiCMOS fabrication process. | [7M] |
| | b) | Show that the switching speed of an enhancement MOSFET varies inversely as the square of the channel length. | [7M] |
| 3. | a) | Give the design rules for the following cases with neat sketches:
(i) Polysilicon – polysilicon (ii) n-type diffusion – n-type diffusion
(iii) n-type diffusion – p-type diffusion (iv) metal 1 – metal 2. | [8M] |
| | b) | Design a stick diagram for two input pMOS NAND and NOR gates. | [6M] |
| 4. | | Describe the following briefly
(i) Cascaded inverters as drivers (ii) Super buffers (iii) BiCMOS drivers | [14M] |
| 5. | a) | Explain the terms controllability, observability and fault coverage. | [7M] |
| | b) | With suitable diagrams, explain the Scan based test techniques. | [7M] |
| 6. | a) | List out the different configuration modes in FPGA. Briefly discuss about it. | [7M] |
| | b) | How the pass transistors are used to connect wire segments for the purpose of FPGA programming? Explain. | [7M] |
| 7. | a) | What is the different technical parameter issues connected with VLSI low power and low voltage design? Explain. | [7M] |
| | b) | With schematic diagrams explain about deep submicron processes. | [7M] |

